



Substitute for form 164BA/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)

Under the Patent Reform Act of 1995, no person is required to respond to a solicitation of information unless it contains a valid OMB control number.

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 4

Attorney Docket No: 303.390US4

	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
<i>for</i>	US-5,897,333	04/27/1999	Goossen, Keith W., et al.	438	455	03/14/1997
<i>for</i>	US-5,900,674	05/04/1999	Wojnarowski, Robert J., et al.	257	774	12/23/1996
<i>for</i>	US-5,901,050	05/04/1999	Imai, Ryuji	361	820	08/21/1997
<i>for</i>	US-5,902,118	05/11/1999	Hubner, Holger	438	106	07/03/1995
<i>for</i>	US-5,903,045	05/11/1999	Bertin, Claude L., et al.	257	621	04/30/1996
<i>for</i>	US-5,915,167	06/22/1999	Leedy, Glenn J.	438	108	04/04/1997
<i>for</i>	US-5,952,665	09/14/1999	Bhargava, R. N.	250	483.1	11/28/1997
<i>for</i>	US-5,963,088	10/05/1999	Czarnul, Z., et al.	330	69	07/29/1997
<i>for</i>	US-6,090,636	07/18/2000	Geusic, Joseph E., et al.	438	31	02/26/1998
<i>for</i>	US-6,122,187	09/19/2001	Ahn, K. Y., et al.	365	63	11/23/1998
<i>for</i>	US-6,143,616	11/07/2000	Geusic, J. E., et al.	438	389	08/22/1997
<i>for</i>	US-6,150,188	11/21/2000	Geusic, J. E., et al.	438	31	02/26/1998
<i>for</i>	US-6,181,864	01/30/2001	Jang, Woo-Hyuk, et al.	385	137	08/13/1998
<i>for</i>	US-6,187,677	02/13/2001	Ahn, K. Y.	438	667	08/22/1997
<i>for</i>	US-6,198,168	03/06/2001	Geusic, J. E., et al.	257	774	01/20/1998
<i>for</i>	US-6,281,042	08/28/2001	Ahn, K. Y., et al.	438	108	08/31/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
<i>for</i>	JP-03-013907	01/22/1991	Tatsuya, S.	G02 B	6/12	
<i>for</i>	JP-04-263462	09/18/1992	Shimizu, Kozo	H01L	25/04	
<i>for</i>	JP-05-145060	06/11/1993	Maaku, Dorainan J.	H01L	29/44	
<i>for</i>	JP-56-055067	05/15/1981	Takagi, Y., et al.	H01L	23/52	
<i>for</i>	WO-91/11833	08/08/1991	Madou, Marc J., et al.	H01 R	9/00	
<i>for</i>	WO-94/05039	03/03/1994	Capps, David A., et al.	H01L	23/48	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>for</i>		FORBES, L., et al., "Resonant Forward-Biased Guard-Ring Diodes for Suppression of Substrate Noise in Mixed-Mode CMOS Circuits", <u>Electronics Letters</u> , 31, (April 1995), 720-721	

EXAMINER

Julius J. Haldorson

DATE CONSIDERED

6/15/2005

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initials of referenced examiner, whether or not identical to the corresponding one in the disclosure. Draw On Through Station U and in correspondence and not identical. Include copy of this form with each communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is checked.

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)

Under the Paperwork Reduction Act of 1995, no charges are imposed to respond to a collection of information unless it carries a valid OMB control number.

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 3 of 4

Attorney Docket No: 303.390US4

		FOSTER, R. , et al., "High Rate Low-Temperature Selective Tungsten", In: <u>Tungsten and Other Refractory Metals for VLSI Applications III</u> , V.A. Wells, ed., Materials Res. Soc., Pittsburgh, PA, (1988), 69-72	
RE		GONG, S. , et al., "Techniques for Reducing Switching Noise in High Speed Digital Systems", <u>Proceedings of the 8th Annual IEEE International ASIC Conference and Exhibit</u> , Austin, TX, (1995), 21-24	
RE		HEAVENS, O. , <u>Optical Properties of Thin Solid Films</u> , Dover Pubs. Inc., New York, (1965), 155-206	
RE		HORIE, H. , et al., "Novel High Aspect Ratio Aluminum Plug for Logic/DRAM LSI's Using Polysilicon-Aluminum Substitute", <u>Technical Digest: IEEE International Electron Devices Meeting</u> , San Francisco, CA, (1996), 946-948	
RE		KIM, Y. S. , et al., "A Study on Pyrolysis DMEAA for Selective Deposition of Aluminum", In: <u>Advanced Metallization and Interconnect Systems for ULSI Applications in 1995</u> , R.C. Ellwanger, et al., (eds.), Materials Research Society, Pittsburgh, PA, (1996), 675-680	
RE		KLAUS, et al., "Atomic Layer Controlled Growth of SiO ₂ Films Using Binary Reaction Sequence Chemistry", <u>Applied Physics Lett.</u> 70(9), (3 March 1997), 1092-94	
RE		LEHMANN, et al., "A Novel Capacitor Technology Based on Porous Silicon", <u>Thin Solid Films</u> 276, Elsevier Science, (1996), 138-42	
RE		LEHMANN, V. , "The Physics of Macropore Formation in Low Doped n-Type Silicon", <u>Journal of the Electrochemical Society</u> , 140(10), (Oct. 1993), 2836-2843	
RE		MASU, K. , et al., "Multilevel Metallization Based on Al CVD", <u>1996 IEEE Symposium on VLSI Technology, Digest of Technical Papers</u> , Honolulu, HI, (June 11-13, 1996), 44-45	
RE		MCCREDIE, B. D. , et al., "Modeling, Measurement, and Simulation of Simultaneous Switching Noise", <u>IEEE Transactions on Components, Packaging, and Manufacturing Technology - Part B</u> , 19, (Aug. 1996), 461-472	
RE		MULLER, K. , et al., "Trench Storage Node Technology for Gigabit DRAM Generations", <u>Digest IEEE International Electron Devices Meeting</u> , San Francisco, CA, (Dec. 1996), 507-510	
RE		OHBA, T. , et al., "Evaluation on Selective Deposition of CVD W Films by Measurement of Surface Temperature", In: <u>Tungsten and Other Refractory Metals for VLSI Applications II</u> , Materials Research Society, Pittsburgh, PA, (1987), 59-66	
RE		OHBA, T. , et al., "Selective Chemical Vapor Deposition of Tungsten Using Silane and Polysilane Reductions", In: <u>Tungsten and Other Refractory Metals for VLSI Applications IV</u> , Materials Research Society, Pittsburgh, PA, (1989), 17-25	
RE		OTT, A W. , et al., "Al ₂ O ₃ Thin Film Growth on Si(100) Using Binary Reaction Sequence Chemistry", <u>Thin Solid Films</u> , Vol. 292, (1997), 135-44	
RE		RAMO, S. , et al., <u>Fields and Waves in Communication Electronics</u> , Third Edition, John Wiley & Sons, Inc., (1994), pp. 428-433	

EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in accordance with MPEP 603. If not in accordance and not considered, include copy of this form with each communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language translation is checked.